

# Surface Mount Schottky Power Rectifier

## Plastic SOD-123 Package

### MBR120ESF, NRVB120ESF

This device uses the Schottky Barrier principle with a large area metal-to-silicon power diode. Ideally suited for low voltage, high frequency rectification or as free wheeling and polarity protection diodes in surface mount applications where compact size and weight are critical to the system. This package also provides an easy to work with alternative to leadless 34 package style. Because of its small size, it is ideal for use in portable and battery powered products such as cellular and cordless phones, chargers, notebook computers, printers, PDAs and PCMCIA cards. Typical applications are AC-DC and DC-DC converters, reverse battery protection, and “Oring” of multiple supply voltages and any other application where performance and size are critical.

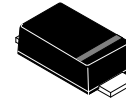
#### Features

- Guardring for Stress Protection
- Low Leakage
- 150°C Operating Junction Temperature
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Package Designed for Optimal Automated Board Assembly
- ESD Rating:
  - ◆ Human Body Model = 3B
  - ◆ Machine Model = C
- NRVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant\*

#### Mechanical Characteristics

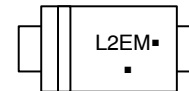
- Device Marking: L2E
- Polarity Designator: Cathode Band
- Weight: 11.7 mg (approximately)
- Case: Epoxy, Molded
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

## SCHOTTKY BARRIER RECTIFIER 1.0 AMPERES 20 VOLTS



SOD-123FL  
CASE 498

#### MARKING DIAGRAM



L2E = Specific Device Code  
M = Date Code  
■ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MBR120ESFT1G	SOD-123FL (Pb-Free)	3,000/ Tape & Reel **
NRVB120ESFT1G	SOD-123FL (Pb-Free)	3,000/ Tape & Reel **
MBR120ESFT3G	SOD-123FL (Pb-Free)	10,000 / Tape & Reel ***
NRVB120ESFT3G	SOD-123FL (Pb-Free)	10,000 / Tape & Reel ***

\*\* 8 mm Tape, 7" Reel

\*\*\* 8 mm Tape, 13" Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# MBR120ESF, NRVB120ESF

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	20	V
Average Rectified Forward Current (At Rated $V_R$ , $T_L = 140^\circ\text{C}$ )	$I_O$	1.0	A
Peak Repetitive Forward Current (At Rated $V_R$ , Square Wave, 20 kHz, $T_L = 125^\circ\text{C}$ )	$I_{FRM}$	2.0	A
Non-Repetitive Peak Surge Current (Non-Repetitive peak surge current, halfwave, single phase, 60 Hz)	$I_{FSM}$	40	A
Storage Temperature	$T_{stg}$	-65 to 150	$^\circ\text{C}$
Operating Junction Temperature	$T_J$	-65 to 150	$^\circ\text{C}$
Voltage Rate of Change (Rated $V_R$ , $T_J = 25^\circ\text{C}$ )	$dv/dt$	10,000	V/ $\mu\text{s}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance – Junction-to-Lead (Note 1)	$R_{tjl}$	26	$^\circ\text{C/W}$
Thermal Resistance – Junction-to-Lead (Note 2)	$R_{tjl}$	21	
Thermal Resistance – Junction-to-Ambient (Note 1)	$R_{tja}$	325	
Thermal Resistance – Junction-to-Ambient (Note 2)	$R_{tja}$	82	

1. Mounted with minimum recommended pad size, PC Board FR4.
2. Mounted with 1 in. copper pad (Cu area 700 mm<sup>2</sup>).

## ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value		Unit
Maximum Instantaneous Forward Voltage (Note 3), See Figure 2	$V_F$	$T_J = 25^\circ\text{C}$	$T_J = 100^\circ\text{C}$	V
( $I_F = 0.1\text{ A}$ )		0.455	0.360	
( $I_F = 1.0\text{ A}$ )		0.530	0.455	
( $I_F = 2.0\text{ A}$ )		0.595	0.540	
Maximum Instantaneous Reverse Current (Note 3), See Figure 4	$I_R$	$T_J = 25^\circ\text{C}$	$T_J = 100^\circ\text{C}$	$\mu\text{A}$
( $V_R = 20\text{ V}$ )		10	1600	
( $V_R = 10\text{ V}$ )		1.0	500	
( $V_R = 5.0\text{ V}$ )		0.5	300	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width  $\leq 250\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

# MBR120ESF, NRVB120ESF

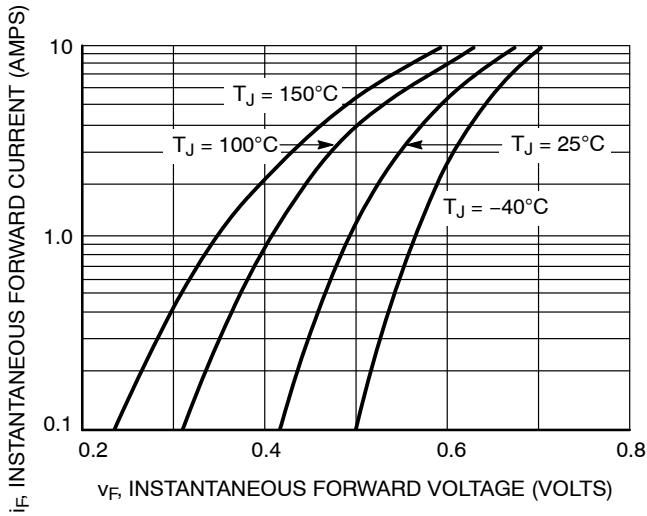


Figure 1. Typical Forward Voltage

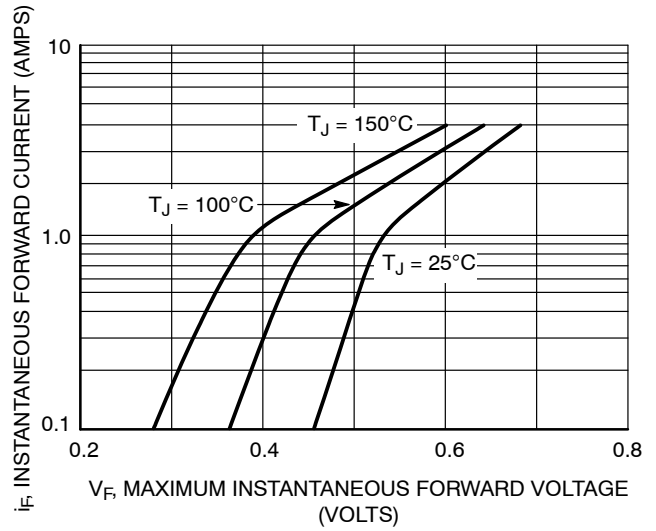


Figure 2. Maximum Forward Voltage

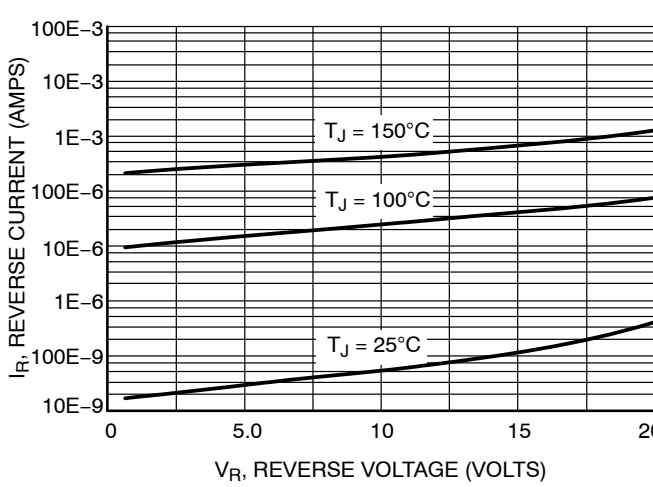


Figure 3. Typical Reverse Current

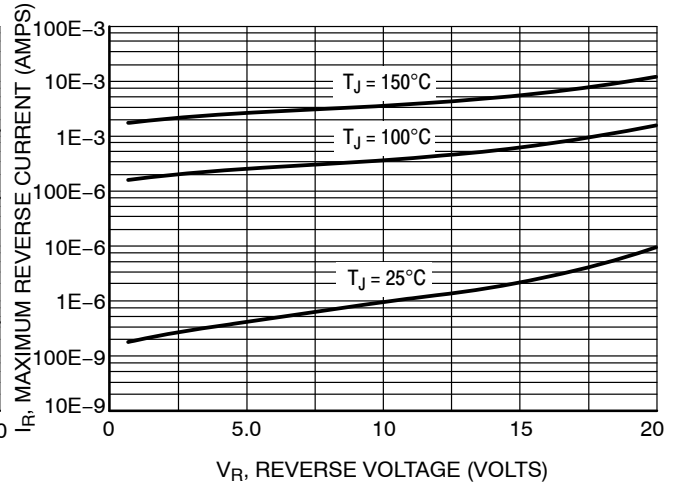


Figure 4. Maximum Reverse Current

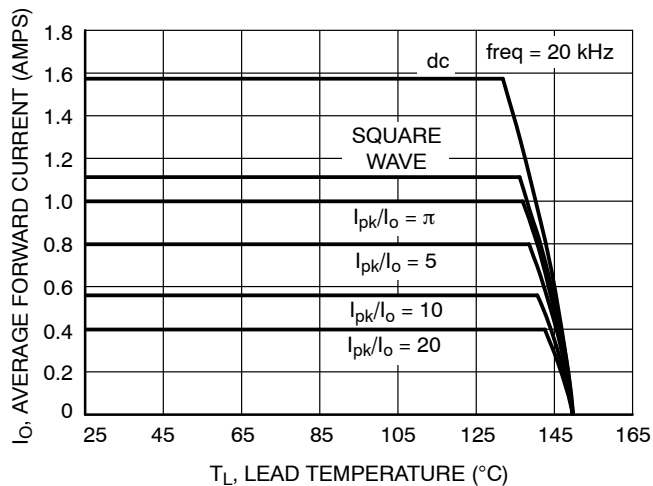


Figure 5. Current Derating

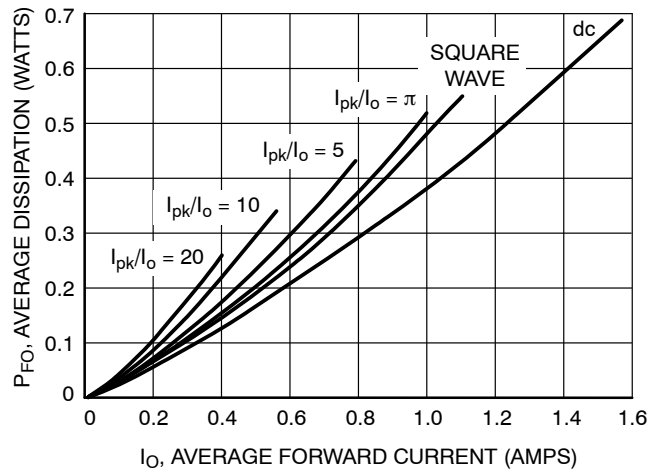


Figure 6. Forward Power Dissipation

# MBR120ESF, NRVB120ESF

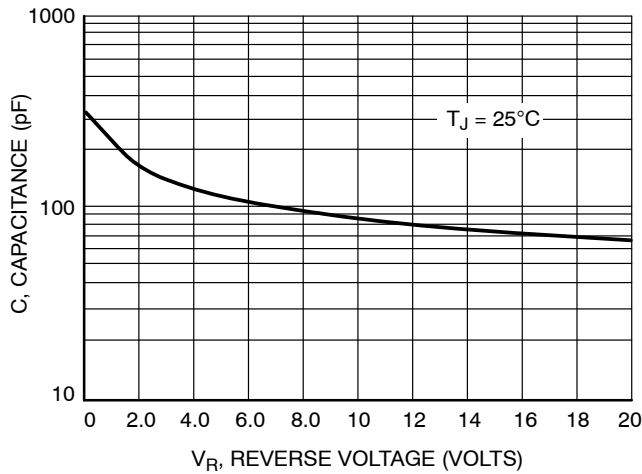


Figure 7. Capacitance

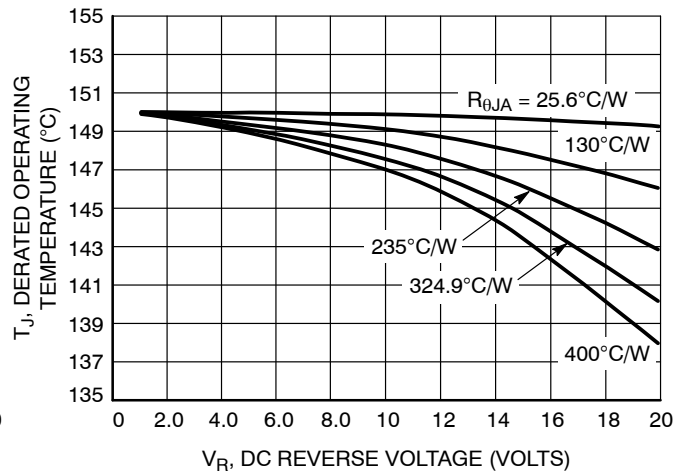


Figure 8. Typical Operating Temperature Derating\*

\* Reverse power dissipation and the possibility of thermal runaway must be considered when operating this device under any reverse voltage conditions. Calculations of  $T_J$  therefore must include forward and reverse power effects. The allowable operating  $T_J$  may be calculated from the equation:

$$T_J = T_{Jmax} - r(t)(P_f + P_r) \text{ where}$$

$r(t)$  = thermal impedance under given conditions,  
 $P_f$  = forward power dissipation, and  
 $P_r$  = reverse power dissipation

This graph displays the derated allowable  $T_J$  due to reverse bias under DC conditions only and is calculated as  $T_J = T_{Jmax} - r(t)P_r$ , where  $r(t) = R_{thja}$ . For other power applications further calculations must be performed.

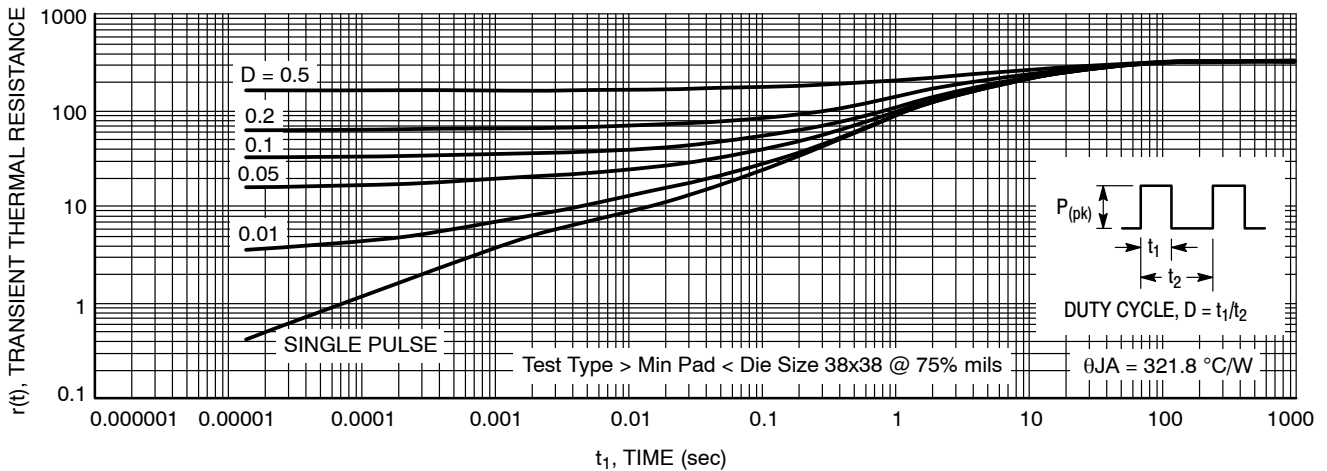
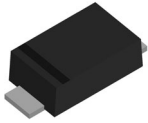
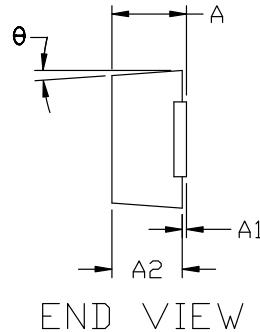
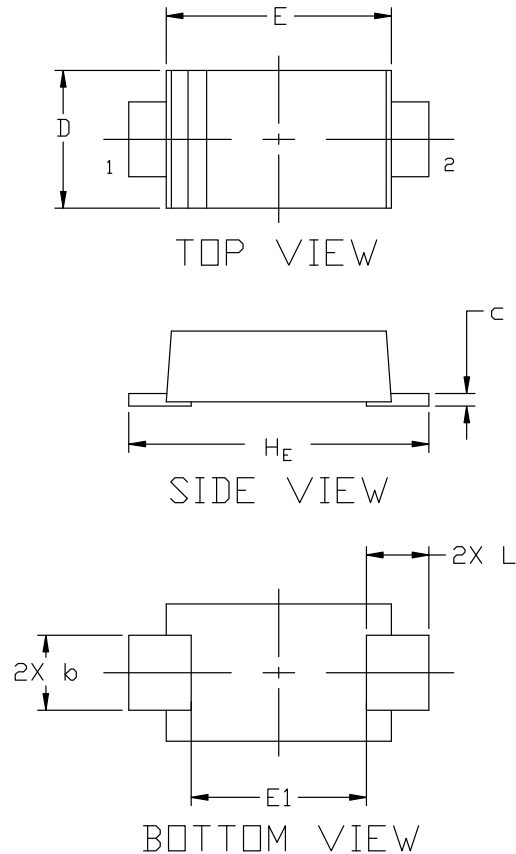


Figure 9. Thermal Response


**SOD-123-2 1.65x2.70x0.90**  
**CASE 498**  
**ISSUE E**

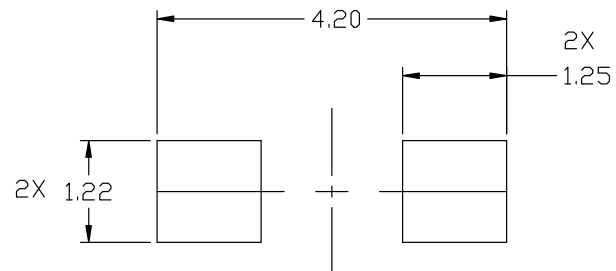
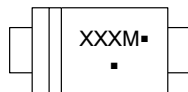
DATE 22 AUG 2023



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	0.95	0.98
A1	0.00	0.05	0.10
A2	0.85	0.90	0.95
b	0.70	0.90	1.10
c	0.10	0.15	0.20
D	1.50	1.65	1.80
E	2.50	2.70	2.90
E1	1.70	2.10	2.50
H <sub>E</sub>	3.40	3.60	3.80
L	0.55	0.75	0.95
θ	0°	---	8°

**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS b AND L ARE TO BE MEASURED ON A FLAT SECTION OF THE LEAD BETWEEN 0.10 AND 0.25 FROM THE LEAD TIP.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH PROTRUSIONS, OR GATE BURRS.
5. FLAT LEAD.


**GENERIC MARKING DIAGRAM\***


XXX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

\* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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